

SN74LV541A 具有三态输出的八路缓冲器/驱动器

1 特性

- 2V 至 5.5V V_{CC} 运行
- 电压为 5V 时, t_{pd} 最大值为 6ns
- V_{OLP} (输出接地反弹) 典型值小于 0.8V ($V_{CC} = 3.3V$ 、 $T_A = 25^\circ C$)
- V_{OHV} (输出 V_{OH} 下冲) 典型值大于 2.3V ($V_{CC} = 3.3V$ 、 $T_A = 25^\circ C$ 时)
- 支持所有端口上的混合模式电压运行
- I_{off} 支持局部断电模式运行
- 闩锁性能超过 250mA, 符合 JESD 17 规范
- ESD 保护性能超过 JESD 22 规范要求
 - 3000V 人体放电模型
 - 2000V 充电器件模型

2 应用

- 智能电网
- 电视
- 机顶盒
- 音频
- 服务器
- 监控摄像头
- 网络交换机
- 信息娱乐系统

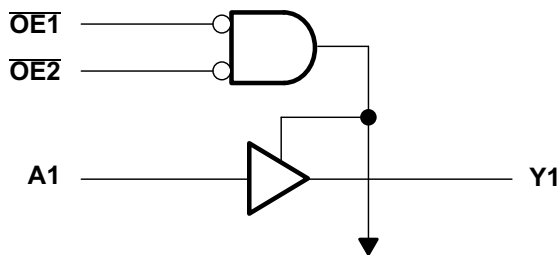
3 说明

SN74LV541A 器件是一款八路缓冲器/驱动器, 可在 2V 至 5.5V V_{CC} 电压下运行。

封装信息⁽¹⁾

器件型号	封装	封装尺寸 (NOM)
SN74LV541A	RGY (VQFN, 20)	4.50mm × 3.50mm
	RKS (VQFN, 20)	4.50mm × 2.50mm
	DB (SSOP, 20)	7.20mm × 5.30mm
	NS (SOP, 20)	12.60mm × 5.30mm
	PW (TSSOP, 20)	6.50mm × 4.40mm
	DGV (TVSOP, 20)	5.00mm × 4.40mm
	DW (SOIC, 20)	12.80mm × 7.50mm
	DGS (VSSOP, 20)	5.10mm × 3.00mm

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。



To Seven Other Channels
简化原理图



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision L (January 2023) to Revision M (March 2023)	Page
• Updated thermal values for DB package from $R_{\theta JA} = 96.0$ to 118.2 , $R_{\theta JC}(\text{top}) = 56.7$ to 77.2 , $R_{\theta JB} = 51.2$ to 73 , $\Psi_{JT} = 19.4$ to 42.2 , $\Psi_{JB} = 50.8$ to 72.6 , all values in $^{\circ}\text{C/W}$	5
• Updated thermal values for NS package from $R_{\theta JA} = 77.1$ to 108.1 , $R_{\theta JC}(\text{top}) = 43.6$ to 73.9 , $R_{\theta JB} = 44.6$ to 73.1 , $\Psi_{JT} = 17.2$ to 44.1 , $\Psi_{JB} = 44.2$ to 72.8 , all values in $^{\circ}\text{C/W}$	5

Changes from Revision K (November 2022) to Revision L (January 2023)	Page
• 向数据表添加了 DGS 封装信息.....	1

Changes from Revision J (December 2014) to Revision K (November 2022)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• 删除了 特性 部分中的 200V 机器放电模型.....	1
• 在数据表中添加了 RKS 封装信息.....	1
• Updated the <i>Pin Functions</i> table.....	3
• Updated the <i>Typical Characteristics</i> section.....	8
• Updated the <i>Functional Block Diagram</i> figure.....	11
• Added the <i>Balanced CMOS 3-State Outputs</i> , <i>Partial Power Down (I_{off})</i> , and <i>Clamp Diode Structure</i> sections.....	11
• Updated the <i>Application Information</i> section.....	13
• Updated the <i>Design Requirements</i> section to include the <i>Power Considerations</i> , <i>Input Considerations</i> , and <i>Output Considerations</i> sections.....	13
• Updated the <i>Detailed Design Procedure</i> section.....	13
• Updated the <i>Layout Example</i> section.....	16

5 Pin Configuration and Functions

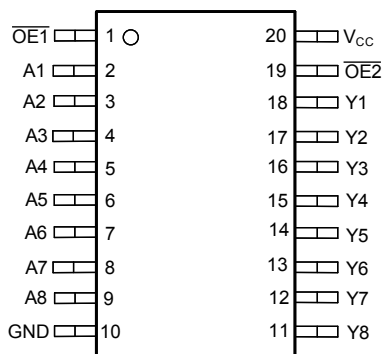


图 5-1. DB, DGV, DW, NS, PW or DGS Package, 20-Pin SSOP, TVSOP, SOIC, SO, TSSOP or VSSOP (Top View)

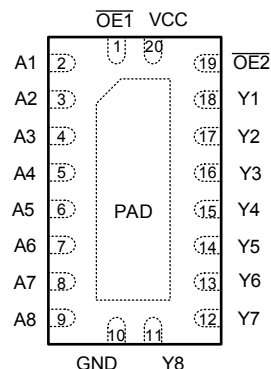


图 5-2. RGY and RKS Package, 20-Pin VQFN with (Exposed Thermal Pad Top View)

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
OE1	1	I	Output enable input 1, active low
A1	2	I	Input for channel 1
A2	3	I	Input for channel 2
A3	4	I	Input for channel 3
A4	5	I	Input for channel 4
A5	6	I	Input for channel 5
A6	7	I	Input for channel 6
A7	8	I	Input for channel 7
A8	9	I	Input for channel 8
GND	10	G	Ground
Y8	11	O	Output for channel 8
Y7	12	O	Output for channel 7
Y6	13	O	Output for channel 6
Y5	14	O	Output for channel 5
Y4	15	O	Output for channel 4
Y3	16	O	Output for channel 3
Y2	17	O	Output for channel 2
Y1	18	O	Output for channel 1
OE2	19	I	Output enable input 2, active low
V _{CC}	20	P	Positive supply
Thermal Pad ⁽²⁾		—	The thermal pad can be connect to GND or left floating. Do not connect to any other signal or supply.

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

(2) RKS package only

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V_{CC}	Supply voltage range	–0.5	7	V
V_I	Input voltage range ⁽²⁾	–0.5	7	V
V_O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	–0.5	7	V
V_O	Output voltage range applied in the high or low state ^{(2) (3)}	–0.5	$V_{CC} + 0.5$	V
I_{IK}	Input clamp current	$V_I < 0$		–20 mA
I_{OK}	Output clamp current	$V_O < 0$		–50 mA
I_O	Continuous output current	$V_O = 0$ to V_{CC}		±35 mA
	Continuous current through V_{CC} or GND			±70 mA
T_{stg}	Storage temperature range	–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under [# 6.3](#) is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) This value is limited to 5.5-V maximum.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	3000
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002, all pins ⁽²⁾	2000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			SN74LV541A		UNIT
			MIN	MAX	
V _{CC}	Supply voltage		2	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5		V
		V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7		
		V _{CC} = 3 V to 3.6 V	V _{CC} × 0.7		
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.7		
V _{IL}	Low-level input voltage	V _{CC} = 2 V		0.5	V
		V _{CC} = 2.3 V to 2.7 V		V _{CC} × 0.3	
		V _{CC} = 3 V to 3.6 V		V _{CC} × 0.3	
		V _{CC} = 4.5 V to 5.5 V		V _{CC} × 0.3	
V _I	Input voltage		0	5.5	V
V _O	Output voltage	High or low state	0	V _{CC}	V
		3-state	0	5.5	
I _{OH}	High-level output current	V _{CC} = 2 V		–50	μA
		V _{CC} = 2.3 V to 2.7 V		–2	mA
		V _{CC} = 3 V to 3.6 V		–8	
		V _{CC} = 4.5 V to 5.5 V		–16	
I _{OL}	Low-level output current	V _{CC} = 2 V		50	μA
		V _{CC} = 2.3 V to 2.7 V		2	mA
		V _{CC} = 3 V to 3.6 V		8	
		V _{CC} = 4.5 V to 5.5 V		16	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 2.3 V to 2.7 V		200	ns/V
		V _{CC} = 3 V to 3.6 V		100	
		V _{CC} = 4.5 V to 5.5 V		20	
T _A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs* (SCBA004).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LV541A								UNIT
		DB	DGV	DW	NS	PW	RGY	RKS	DGS	
		20 PINS								
R _{θJA}	Junction-to-ambient thermal resistance	118.2	116.1	79.8	108.1	102.8	35.1	75.2	125.5	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	77.2	31.3	45.8	73.9	36.8	43.3	79.4	80.0	
R _{θJB}	Junction-to-board thermal resistance	73	57.6	47.4	73.1	53.8	12.9	47.8	63.8	
Ψ _{JT}	Junction-to-top characterization parameter	42.2	1.0	18.5	44.1	2.5	0.9	14.6	8.4	
Ψ _{JB}	Junction-to-board characterization parameter	72.6	56.9	47.0	72.8	53.3	12.9	47.8	79.9	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	7.9	31.5	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report (SPRA953).

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH}	I _{OH} = –50 µA	2 V to 5.5 V	V _{CC} – 0.1			V _{CC} – 0.1		V _{CC} – 0.1		V
	I _{OH} = –2 mA	2.3 V	2			2		2		
	I _{OH} = –8 mA	3 V	2.48			2.48		2.48		
	I _{OH} = –16 mA	4.5 V	3.8			3.8		3.8		
V _{OL}	I _{OL} = 50 µA	2 V to 5.5 V			0.1		0.1		0.1	V
	I _{OL} = 2 mA	2.3 V			0.4		0.4		0.4	
	I _{OL} = 8 mA	3 V			0.44		0.44		0.44	
	I _{OL} = 16 mA	4.5 V			0.55		0.55		0.55	
I _I	V _I = 5.5 V or GND	0 to 5.5 V			±1		±1		±1	µA
I _{OZ}	V _O = V _{CC} or GND	5.5 V			±5		±5		±5	µA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5 V			20		20		20	µA
I _{off}	V _I or V _O = 0 to 5.5 V	0			5		5		5	µA
C _i	V _I = V _{CC} or GND	3.3 V		2						pF

6.6 Switching Characteristics, V_{CC} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	C _L = 15 pF		6.7	11.3	1	13.5	1	13.5	ns
t _{en}	OE	Y			8.5	16.6	1	19.5	1	19.5	
t _{dis}	OE	Y			8.4	13.1	1	15	1	15	
t _{pd}	A	Y	C _L = 50 pF		8.7	15.9	1	18.5	1	18.5	ns
t _{en}	OE	Y			10.5	20.7	1	24	1	24	
t _{dis}	OE	Y			12.3	17.9	1	20	1	20	
t _{sk(o)}						2		2		2	

6.7 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	C _L = 15 pF		4.8	7	1	8.5	1	8.5	ns
t _{en}	OE	Y			6.1	10.5	1	12.5	1	12.5	
t _{dis}	OE	Y			5.8	11	1	12	1	12	
t _{pd}	A	Y	C _L = 50 pF		6.1	10.5	1	12	1	12	ns
t _{en}	OE	Y			7.4	14	1	16	1	16	
t _{dis}	OE	Y			8.8	15.4	1	17.5	1	17.5	
t _{sk(o)}						1.5		1.5		1.5	

6.8 Switching Characteristics, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	$T_A = 25^\circ\text{C}$			$-40^\circ\text{C to } 85^\circ\text{C}$		$-40^\circ\text{C to } 125^\circ\text{C}$		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	$C_L = 15\text{ pF}$	3.5	5		1	6	1	6	ns
t_{en}	$\overline{OE}$	Y		4.3	7.2		1	8.5	1	8.5	
t_{dis}	$\overline{OE}$	Y		3.9	7.5		1	8	1	8	
t_{pd}	A	Y	$C_L = 50\text{ pF}$	4.3	7		1	8	1	8	ns
t_{en}	$\overline{OE}$	Y		5.3	9.2		1	10.5	1	10.5	
t_{dis}	$\overline{OE}$	Y		5.6	8.8		1	10	1	10	
$t_{sk(o)}$					1			1		1	

6.9 Noise Characteristics

$V_{CC} = 3.3\text{ V}$, $C_L = 50\text{ pF}$, $T_A = 25^\circ\text{C}$ ⁽¹⁾

PARAMETER		SN74LV541A			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.5	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		−0.4	−0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		2.9		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

(1) Characteristics are for surface-mount packages only.

6.10 Operating Characteristics

$T_A = 25^\circ\text{C}$

PARAMETER			TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	Outputs enabled	$C_L = 50\text{ pF}$, $f = 10\text{ MHz}$	3.3 V	16.3	pF
				5 V	17.8	

6.11 Typical Characteristics

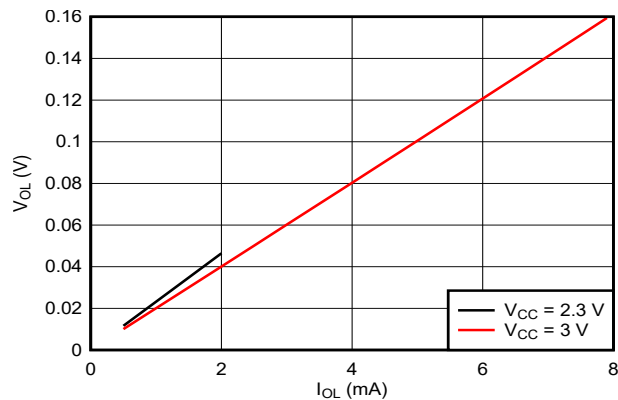


图 6-1. Output Voltage in LOW State, 2.3- and 3-V Supply

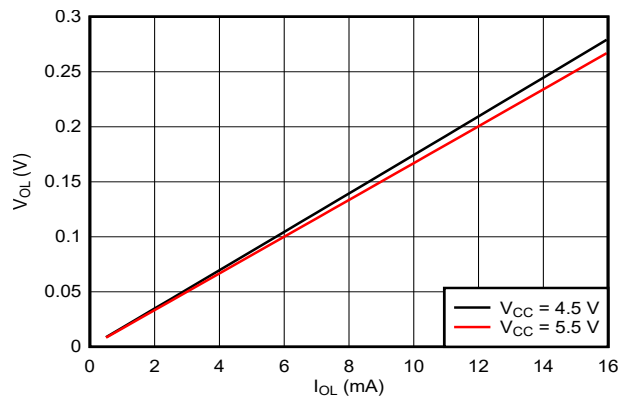


图 6-2. Output Voltage in LOW State, 4.5- and 5.5-V Supply

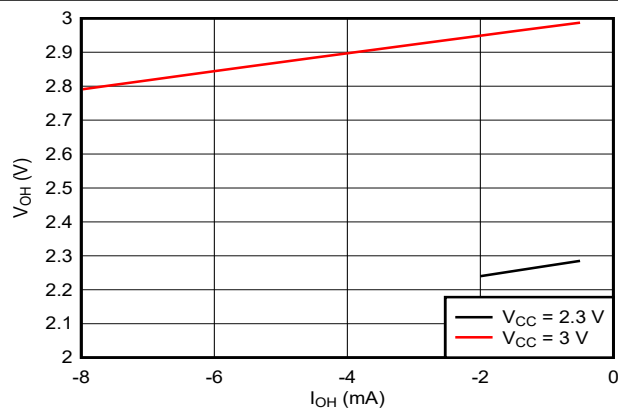


图 6-3. Output Voltage in HIGH State, 2.3- and 3-V Supply

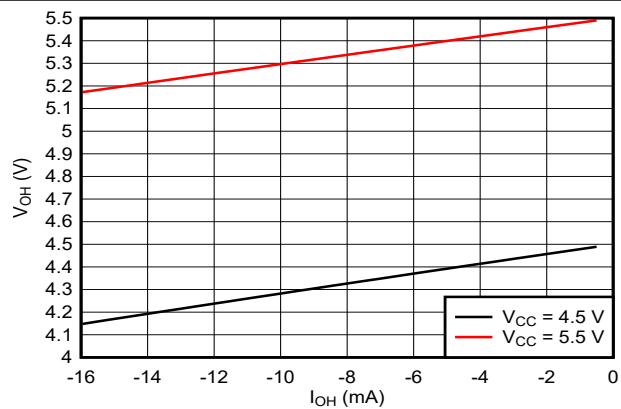


图 6-4. Output Voltage in HIGH State, 4.5- and 5.5-V Supply

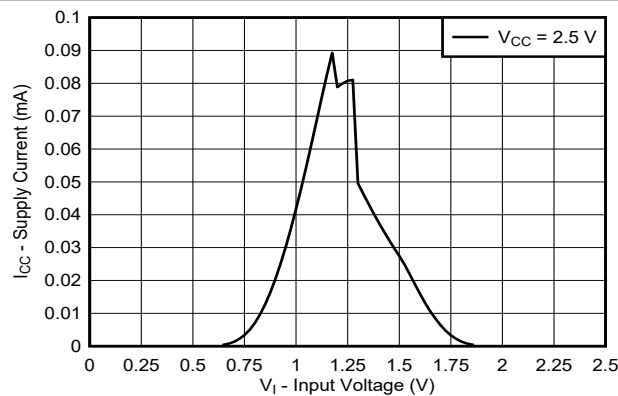


图 6-5. Supply Current Across Input Voltage, 2.5-V Supply

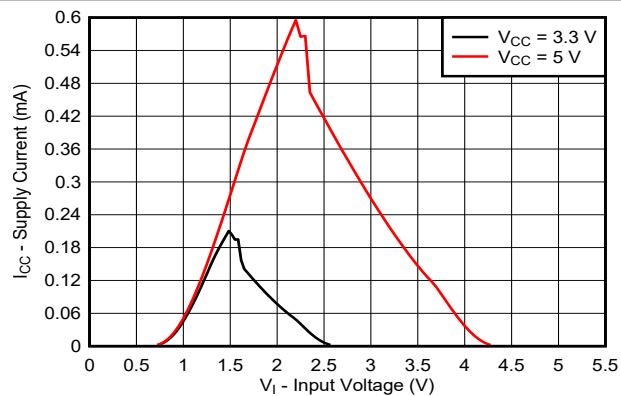


图 6-6. Supply Current Across Input Voltage, 3.3- and 5-V Supply

6.11 Typical Characteristics (continued)

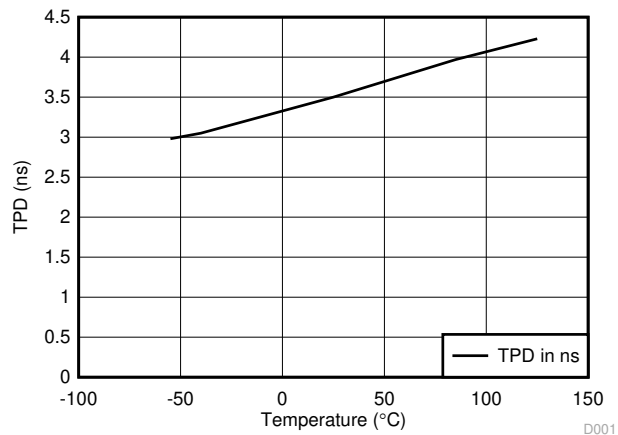


图 6-7. TPD vs Temperature

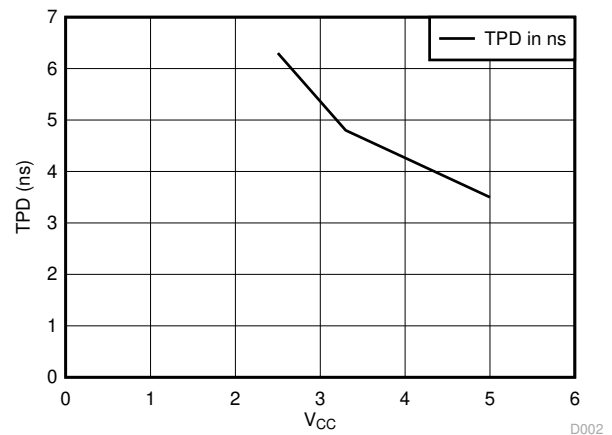
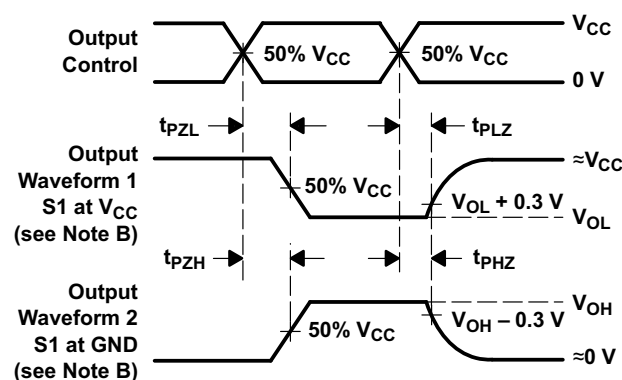
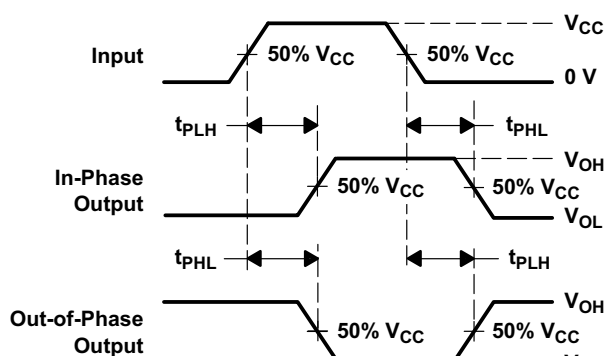
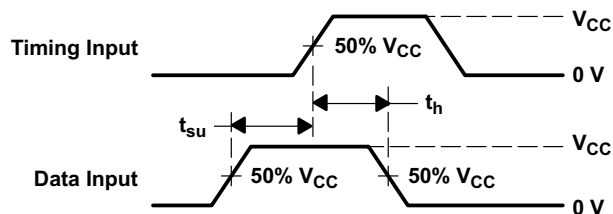
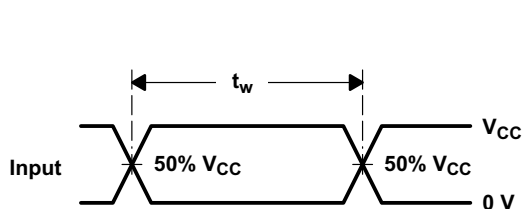
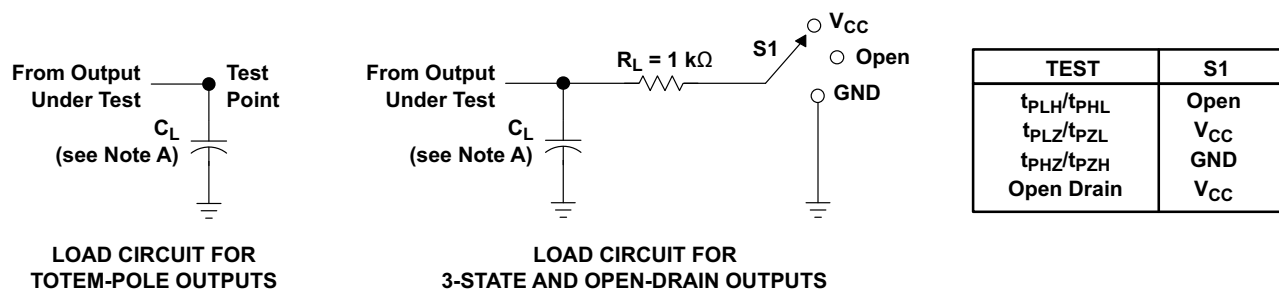


图 6-8. TPD vs VCC at 25°C

7 Parameter Measurement Information



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 3 \text{ ns}$, $t_f \leq 3 \text{ ns}$.
 - D. The outputs are measured one at a time, with one input transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PHL} and t_{PLH} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LV541A device is an octal buffers/driver designed for 2-V to 5.5-V V_{CC} operation.

The SN74LV541A device is ideal for driving bus lines or buffer memory address registers. It features inputs and outputs on opposite sides of the package to facilitate printed circuit board layout.

The 3-state control gate is a two-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all corresponding outputs are in the high-impedance state. The outputs provide non-inverted data when they are not in the high-impedance state.

To ensure the high-impedance state during power up or power down, both $\overline{OE}$ should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LV541A device are fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

8.2 Functional Block Diagram

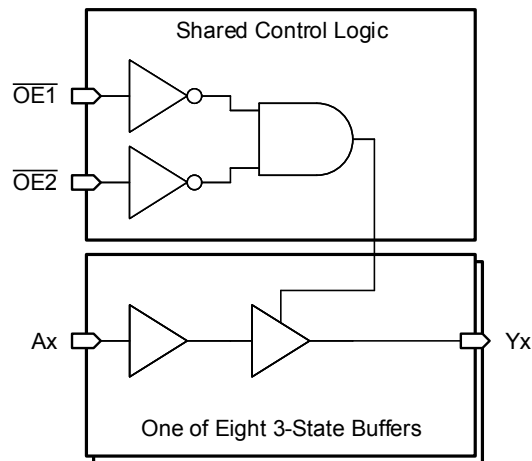


图 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10-k Ω resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

8.3.2 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

8.3.3 Clamp Diode Structure

图 8-2 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

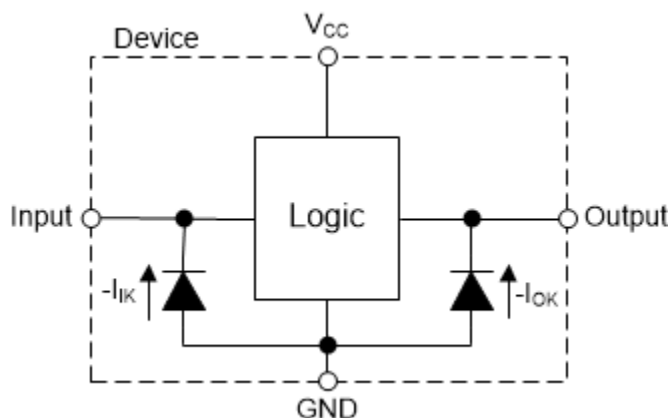


图 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

表 8-1. Function Table
(Each Buffer or Driver)

INPUTS			OUTPUT Y
OE1	OE2	A	
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

The SN74LV541A can be used to drive signals over relatively long traces or transmission lines. In order to reduce ringing caused by impedance mismatches between the driver, transmission line, and receiver, a series damping resistor placed in series with the transmitter's output can be used. The figure in the Application Curve section shows the received signal with three separate resistor values. Just a small amount of resistance can make a significant impact on signal integrity in this type of application.

9.2 Typical Application

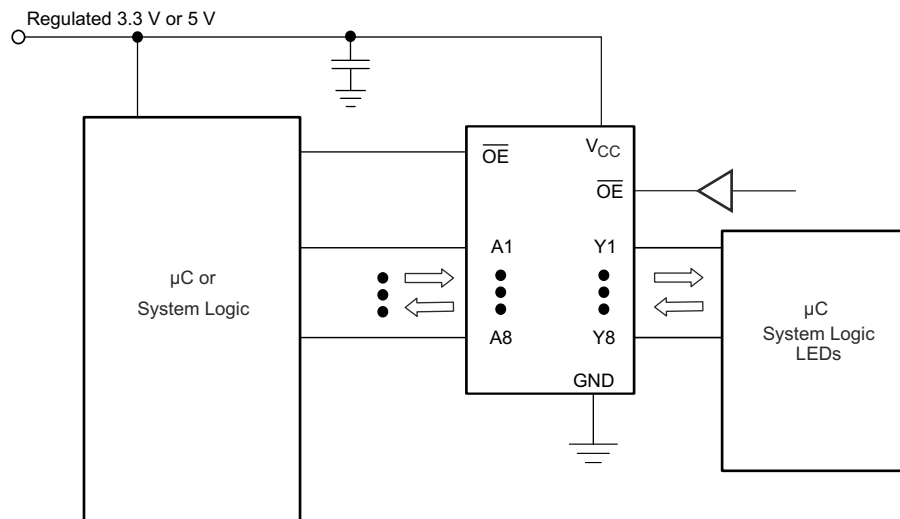


图 9-1. Typical Application Schematic

9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV541A plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV541A plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV541A can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV541A can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV541A (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74LV541A has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.4 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV541A to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.5 Application Curves

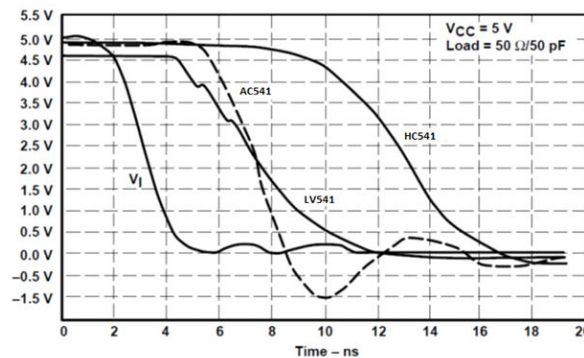


图 9-2. Switching Characteristics Comparison

9.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μF is recommended. If there are multiple V_{CC} pins, 0.01 μF or 0.022 μF is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μF and 1 μF are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

9.4 Layout

9.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in [Figure 9-3](#) are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} , whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

9.4.2 Layout Example

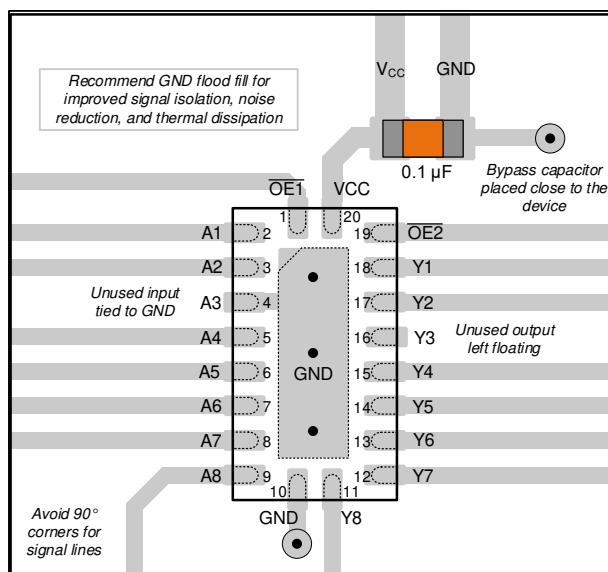


图 9-3. Layout Example for the SN74LV541A in the RKS package

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation](#)
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs application notes](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#)

10.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](https://www.ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.3 支持资源

[TI E2E™ 支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

10.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

10.6 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

10.7 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV541ADBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV541A	Samples
SN74LV541ADBRE4	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV541A	Samples
SN74LV541ADGSR	ACTIVE	VSSOP	DGS	20	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L541A	Samples
SN74LV541ADWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV541A	Samples
SN74LV541ANSR	ACTIVE	SO	NS	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	74LV541A	Samples
SN74LV541APWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LV541A	Samples
SN74LV541APWRG4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV541A	Samples
SN74LV541ARGYR	ACTIVE	VQFN	RGY	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LV541A	Samples
SN74LV541ARKSR	ACTIVE	VQFN	RKS	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV541A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LV541A :

- Automotive : [SN74LV541A-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



*All dimensions are nominal

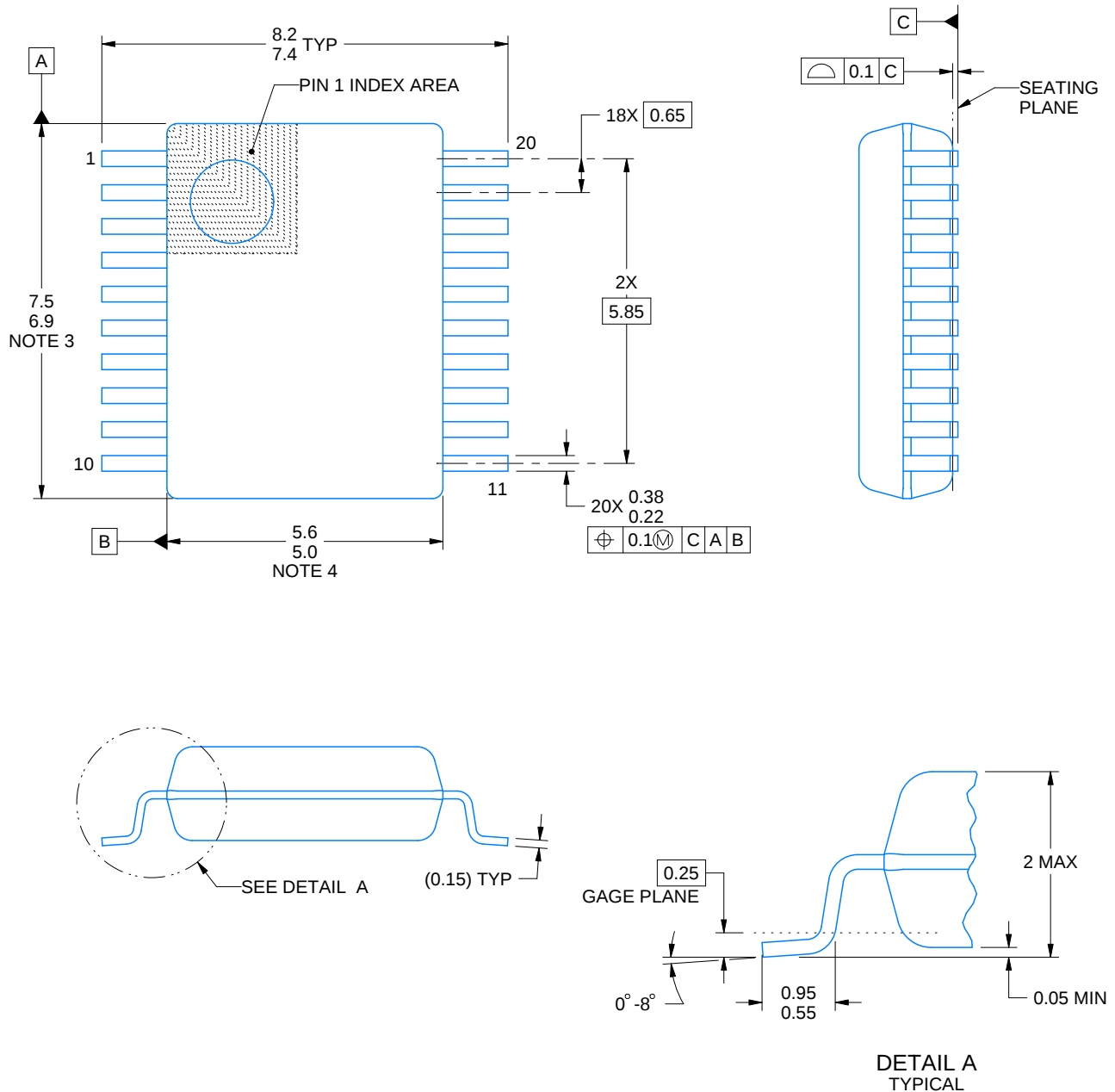
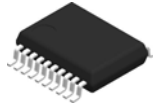
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV541ADBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74LV541ADGSR	VSSOP	DGS	20	5000	330.0	16.4	5.4	5.4	1.45	8.0	16.0	Q1
SN74LV541ADWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74LV541ANSR	SO	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74LV541APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LV541APWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN74LV541APWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74LV541ARGYR	VQFN	RGY	20	3000	330.0	12.4	3.8	4.8	1.6	8.0	12.0	Q1
SN74LV541ARKSR	VQFN	RKS	20	3000	180.0	12.4	2.8	4.8	1.2	4.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV541ADBR	SSOP	DB	20	2000	356.0	356.0	35.0
SN74LV541ADGSR	VSSOP	DGS	20	5000	356.0	356.0	35.0
SN74LV541ADWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN74LV541ANSR	SO	NS	20	2000	367.0	367.0	45.0
SN74LV541APWR	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LV541APWR	TSSOP	PW	20	2000	364.0	364.0	27.0
SN74LV541APWRG4	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74LV541ARGYR	VQFN	RGY	20	3000	356.0	356.0	35.0
SN74LV541ARKSR	VQFN	RKS	20	3000	210.0	185.0	35.0



4214851/B 08/2019

NOTES:

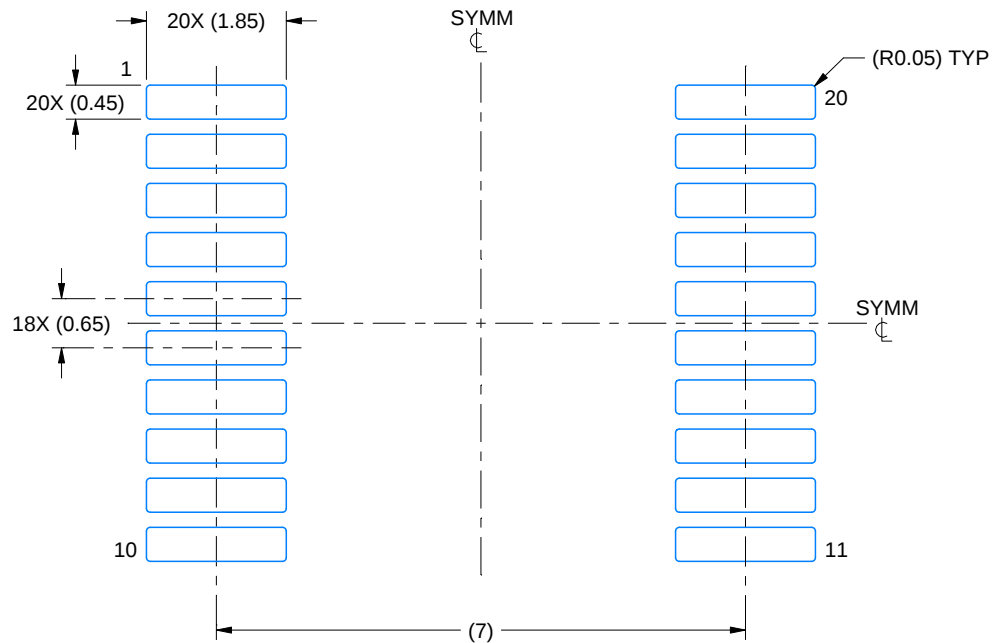
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.

EXAMPLE BOARD LAYOUT

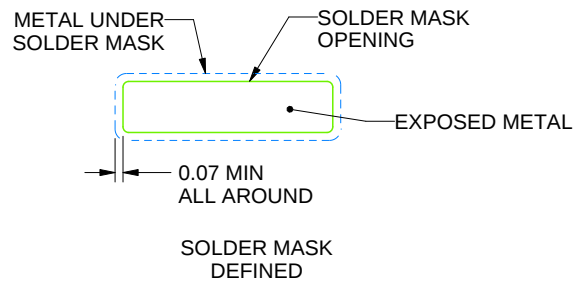
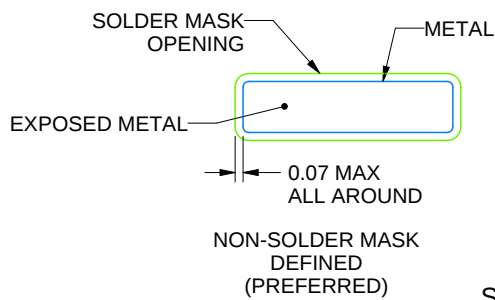
DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4214851/B 08/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

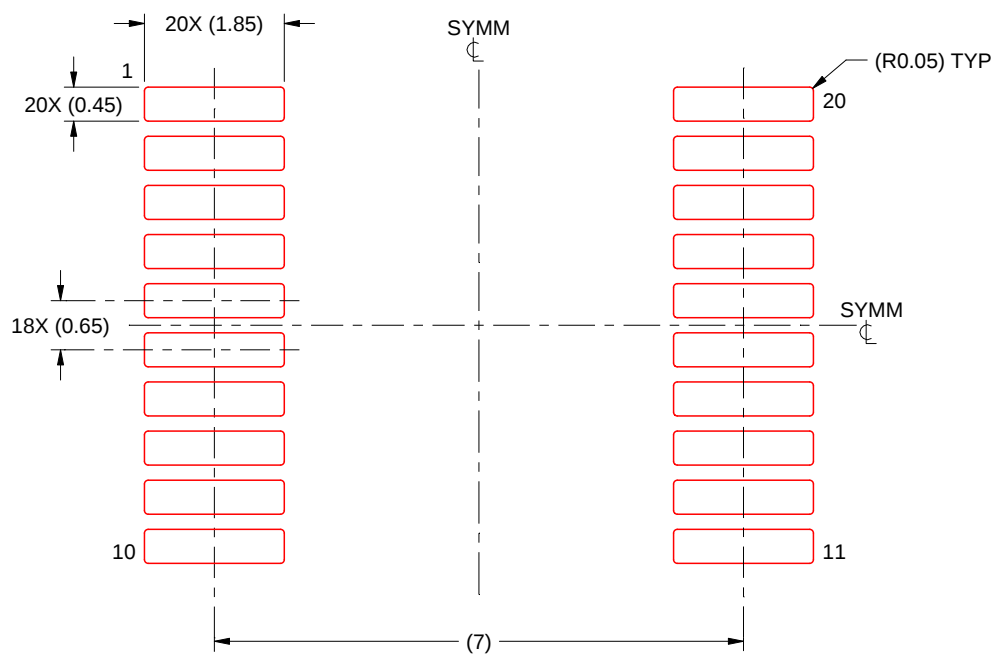
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4214851/B 08/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

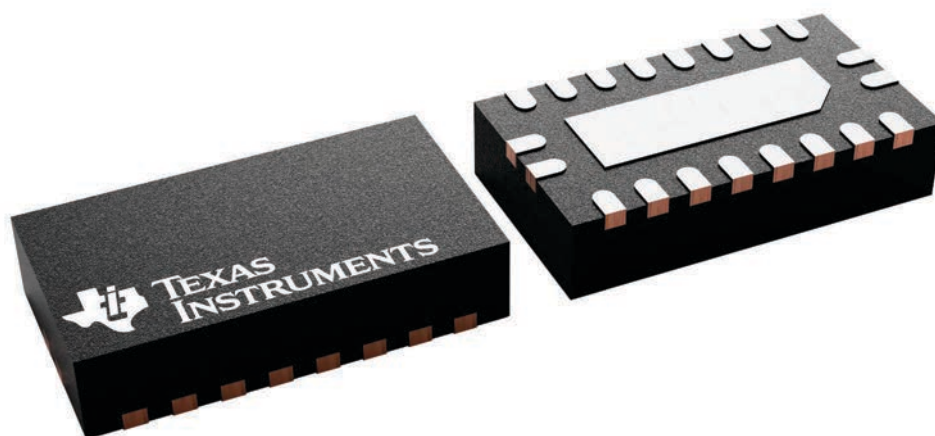
RKS 20

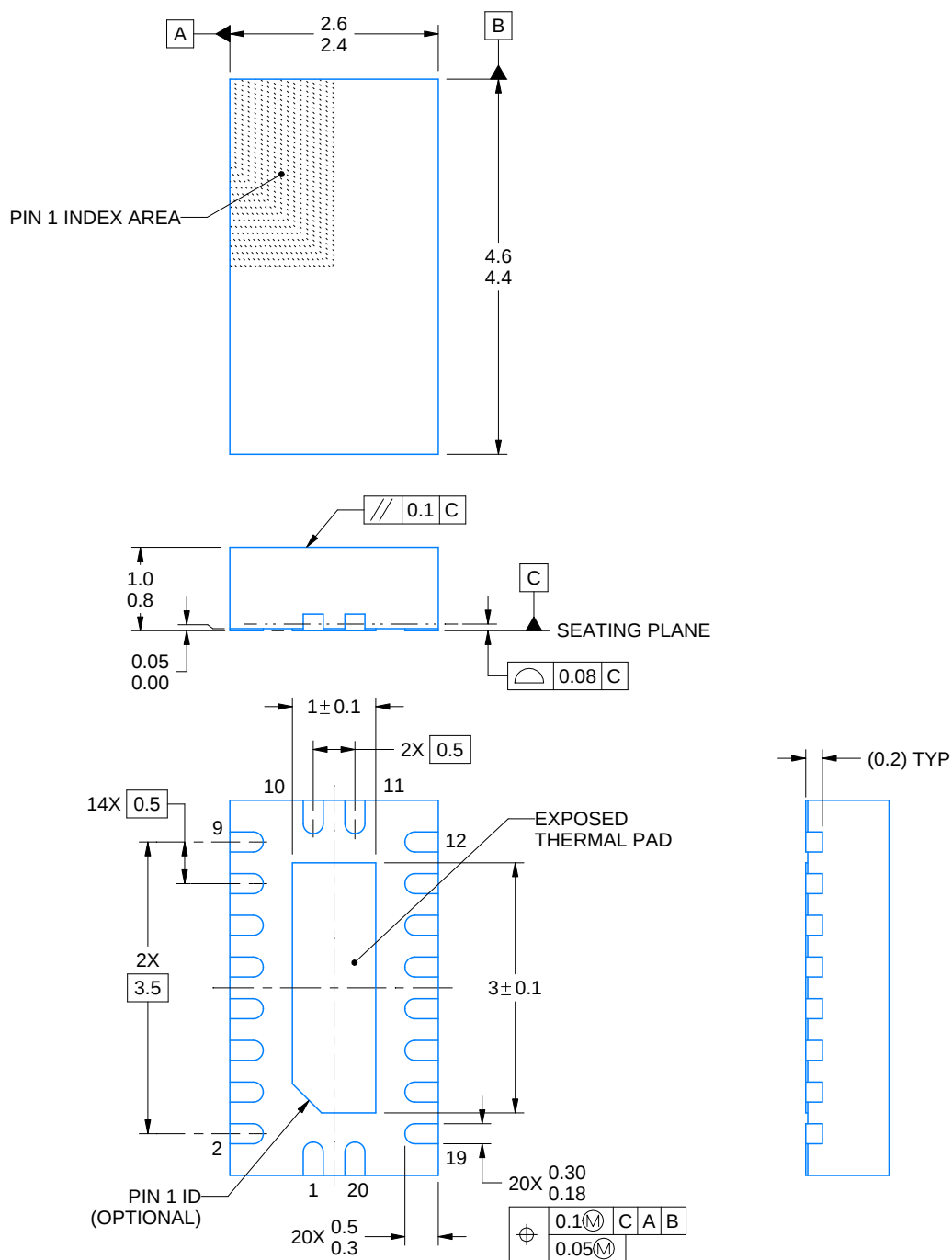
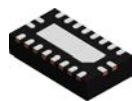
VQFN - 1 mm max height

2.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.





4222490/B 02/2021

NOTES:

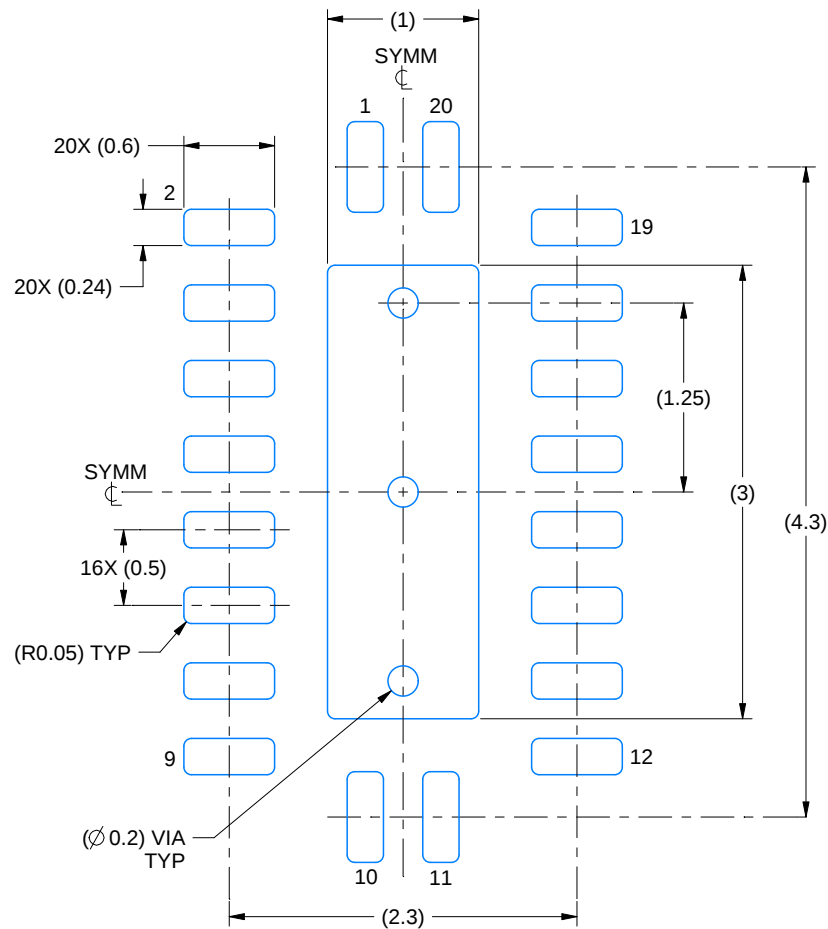
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

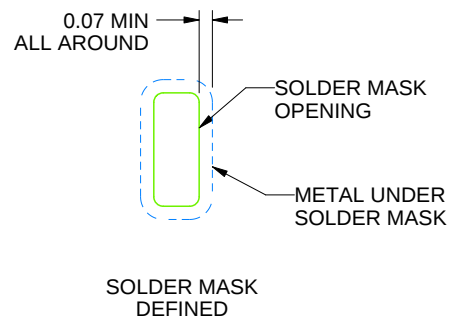
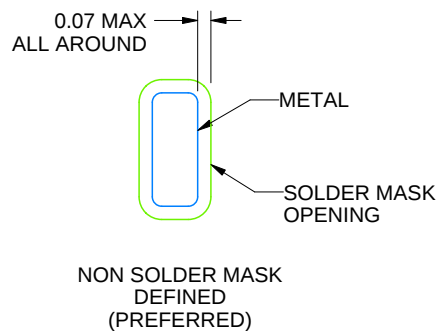
RKS0020A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
SCALE:20X



SOLDER MASK DETAILS

4222490/B 02/2021

NOTES: (continued)

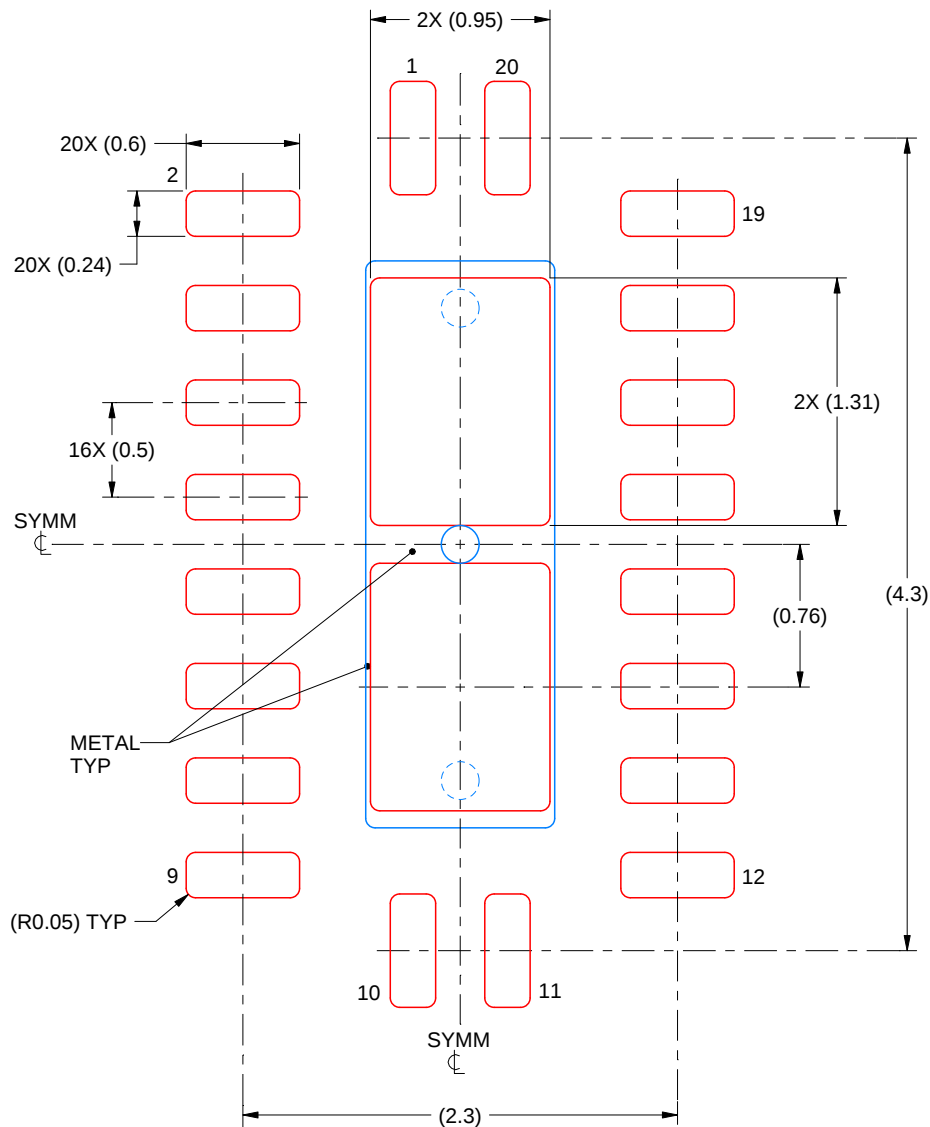
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

EXAMPLE STENCIL DESIGN

RKS0020A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
83% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4222490/B 02/2021

NOTES: (continued)

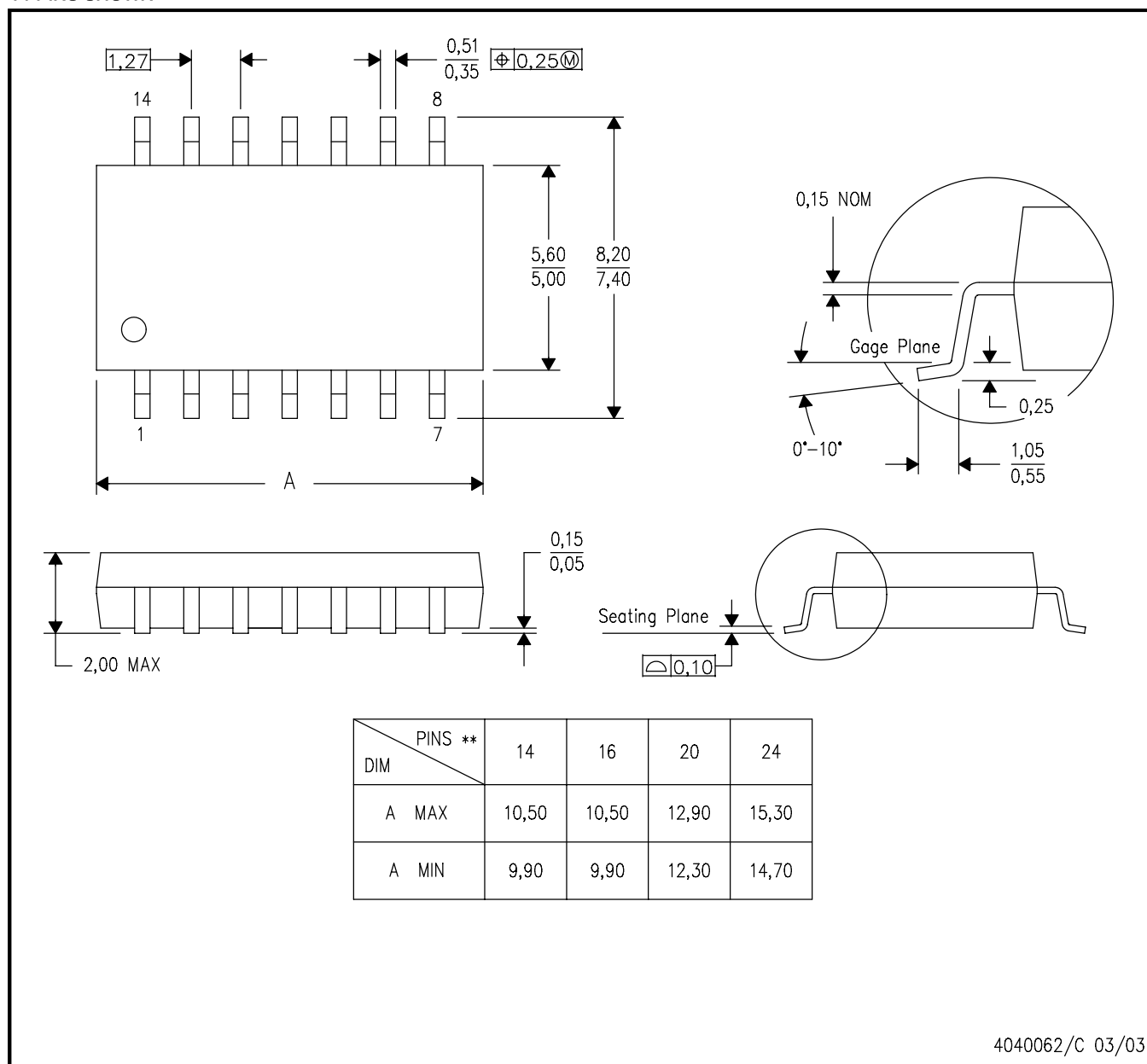
6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

MECHANICAL DATA

NS (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

GENERIC PACKAGE VIEW

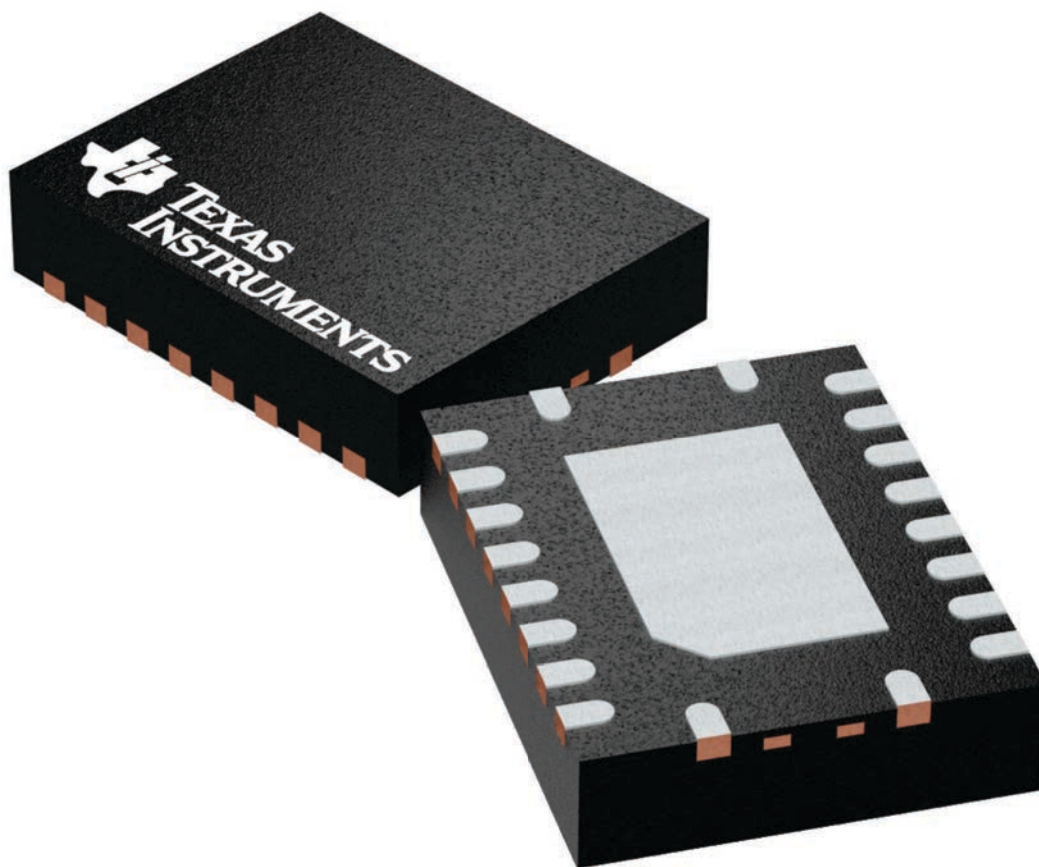
RGY 20

VQFN - 1 mm max height

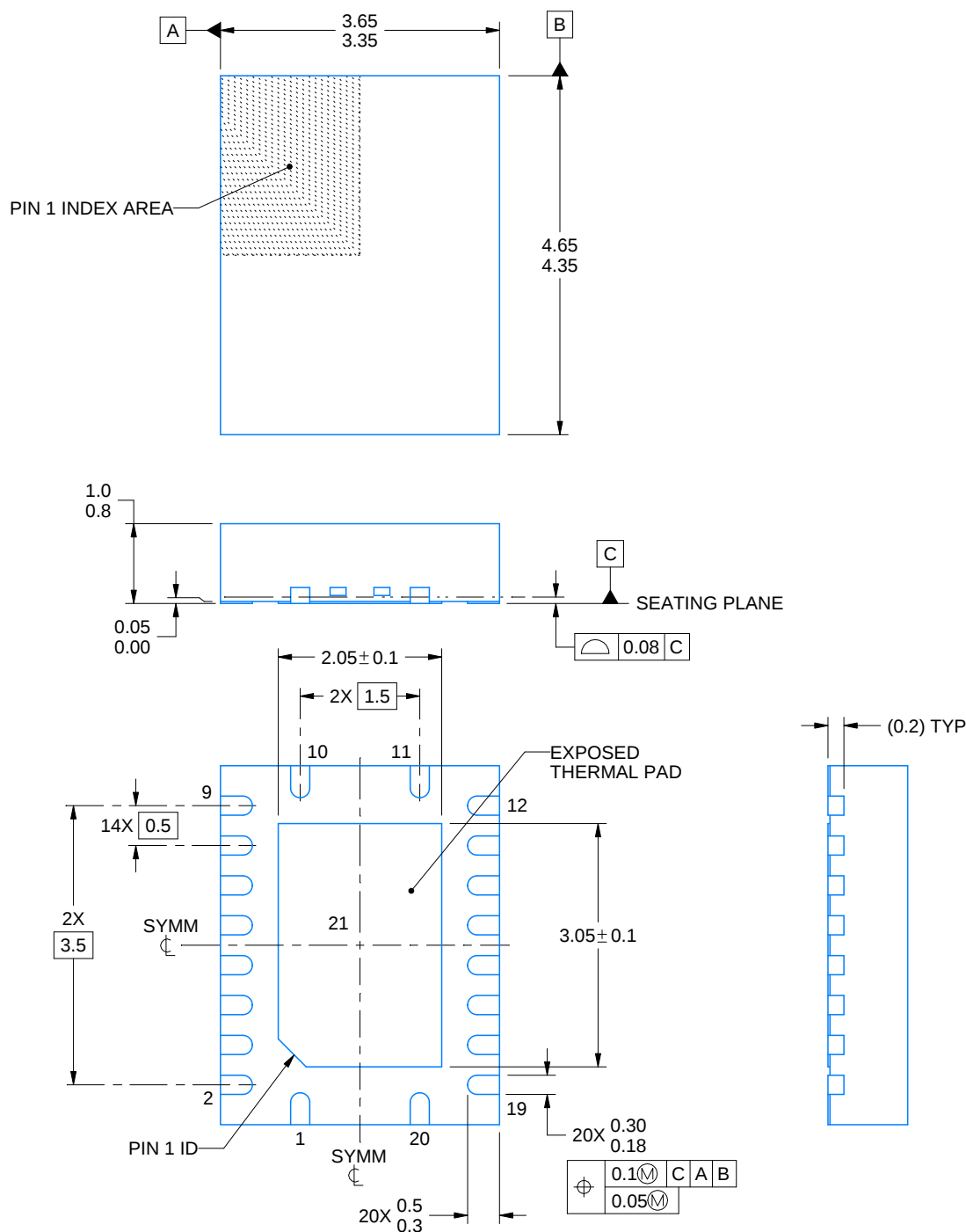
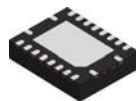
3.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FGLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4225264/A



4225320/A 09/2019

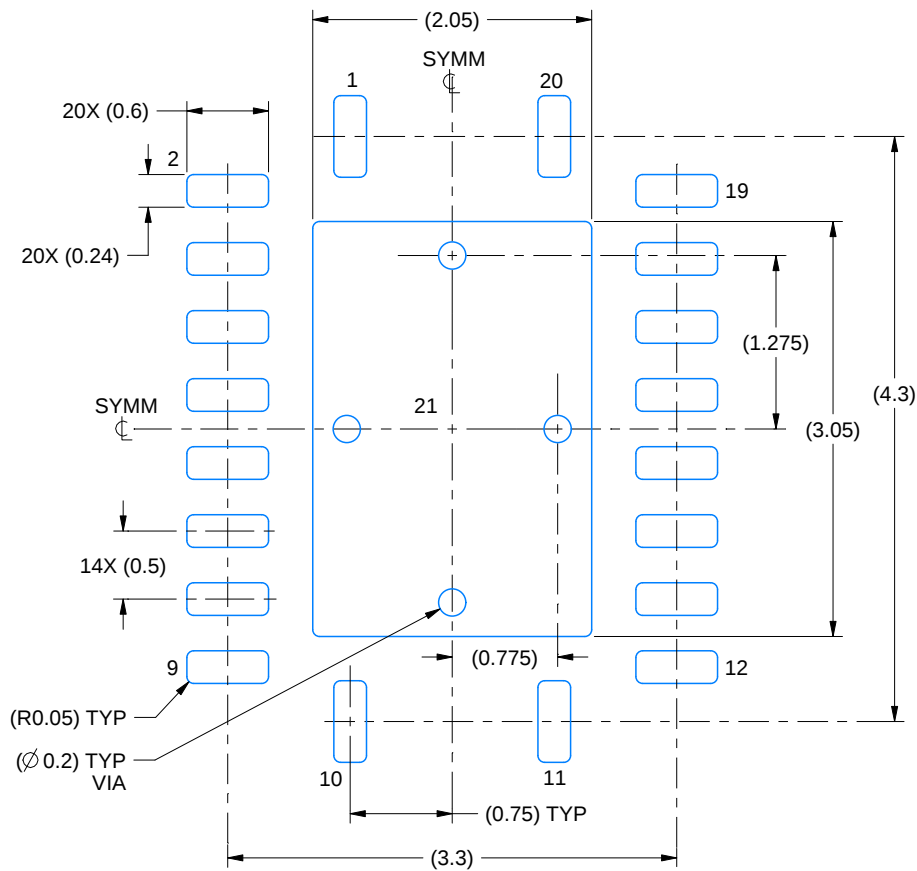
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

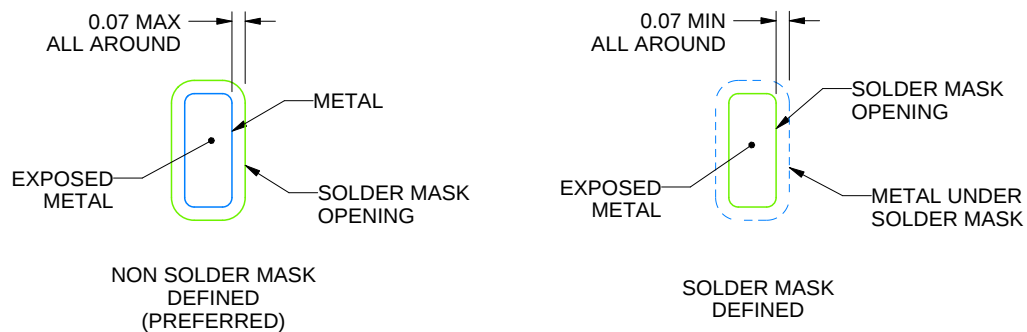
RGY0020A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4225320/A 09/2019

NOTES: (continued)

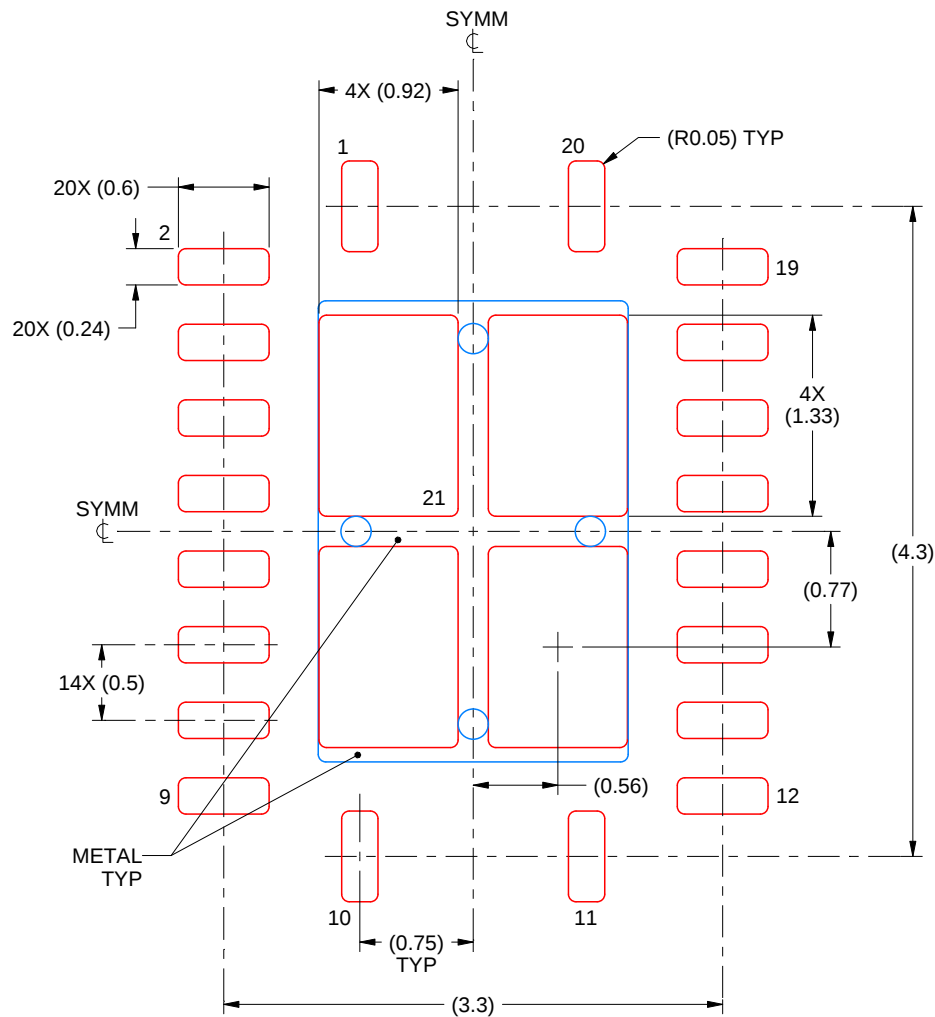
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RGY0020A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



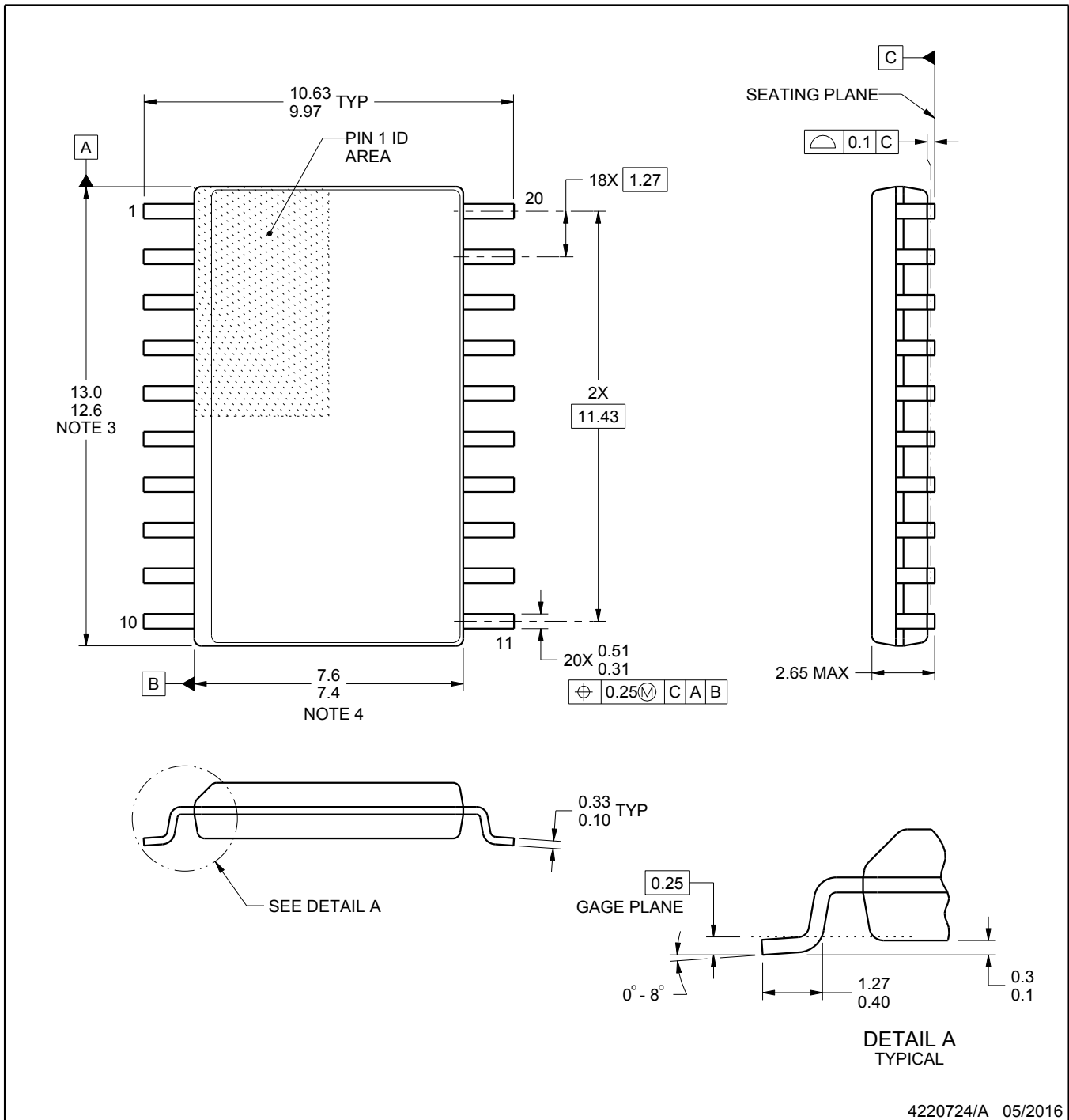
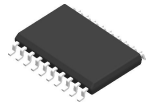
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 21
78% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:20X

4225320/A 09/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



NOTES:

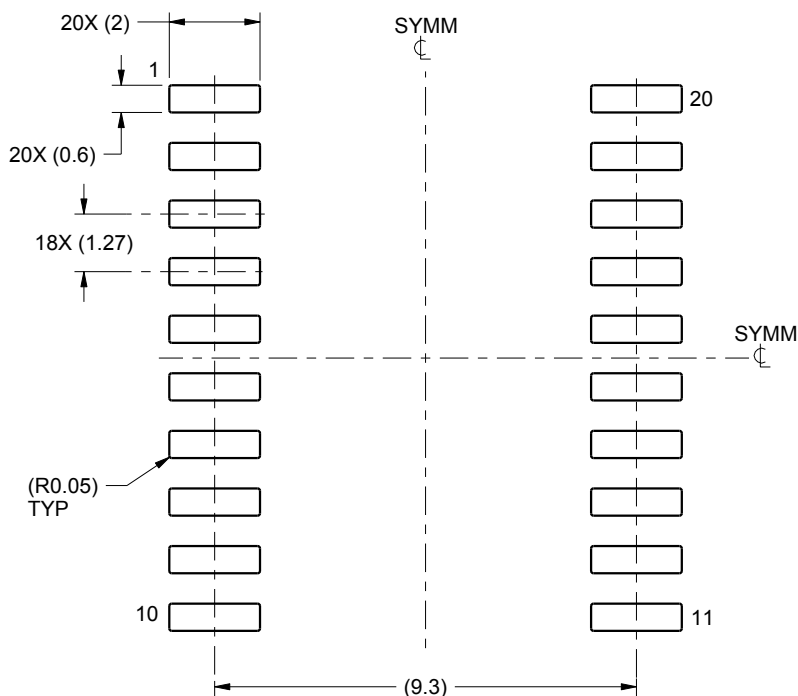
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

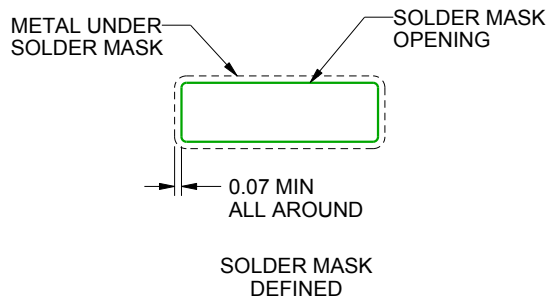
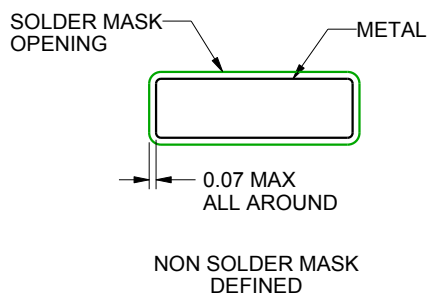
DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:6X



SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

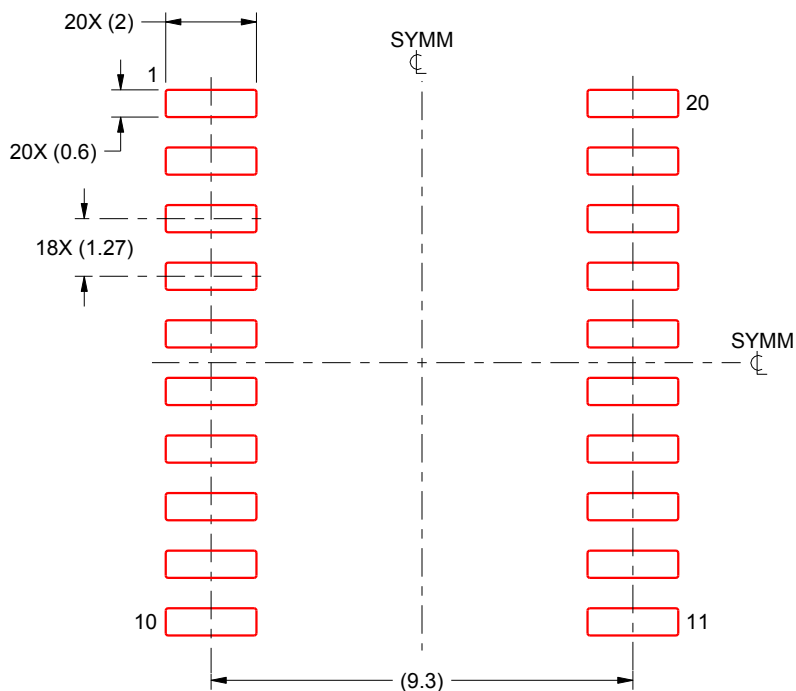
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC

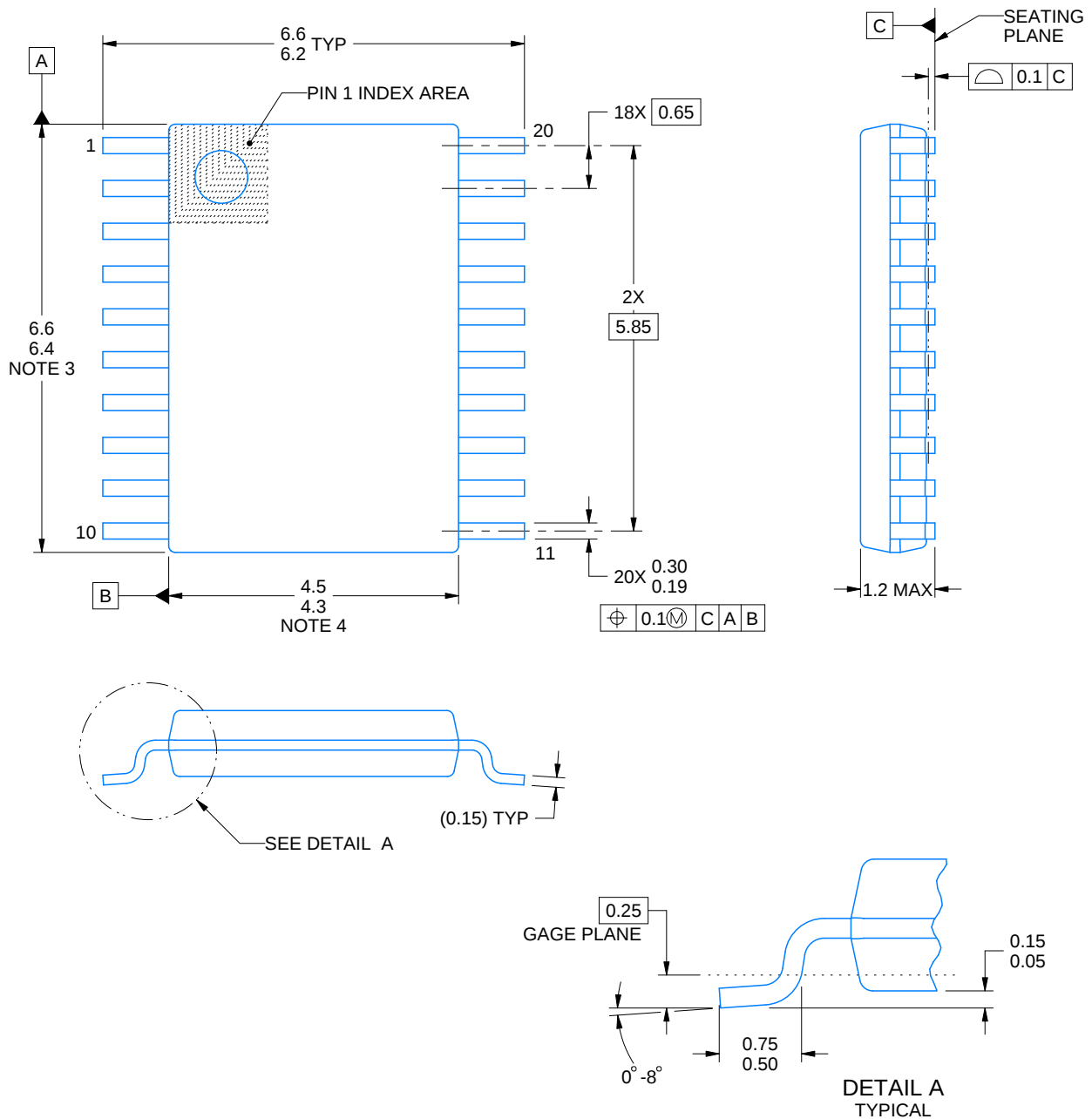
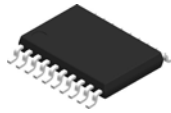


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4220206/A 02/2017

NOTES:

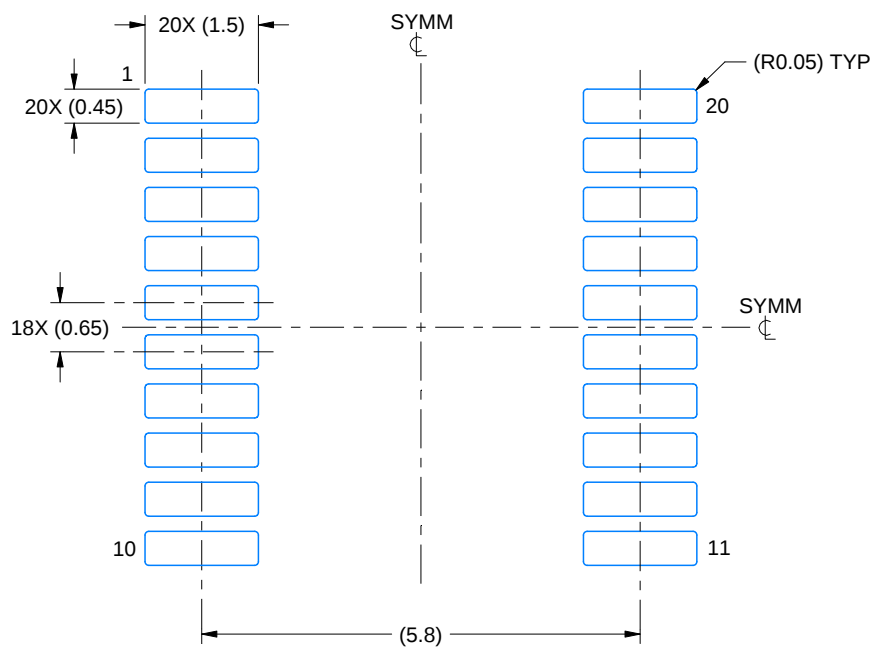
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

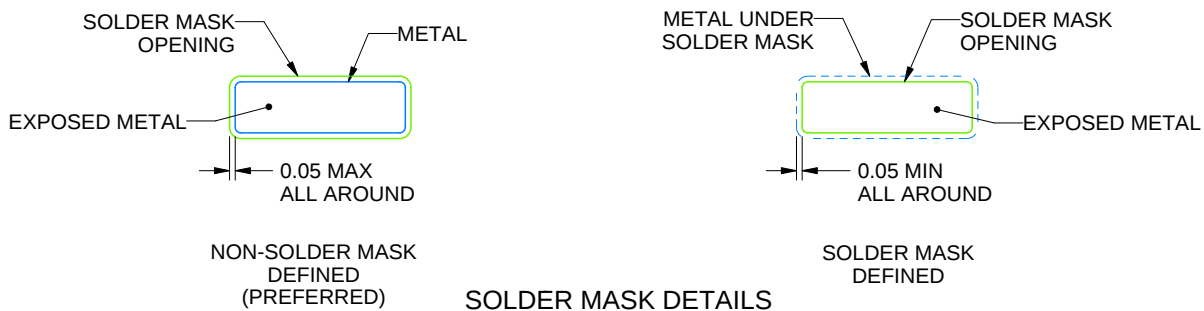
PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220206/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

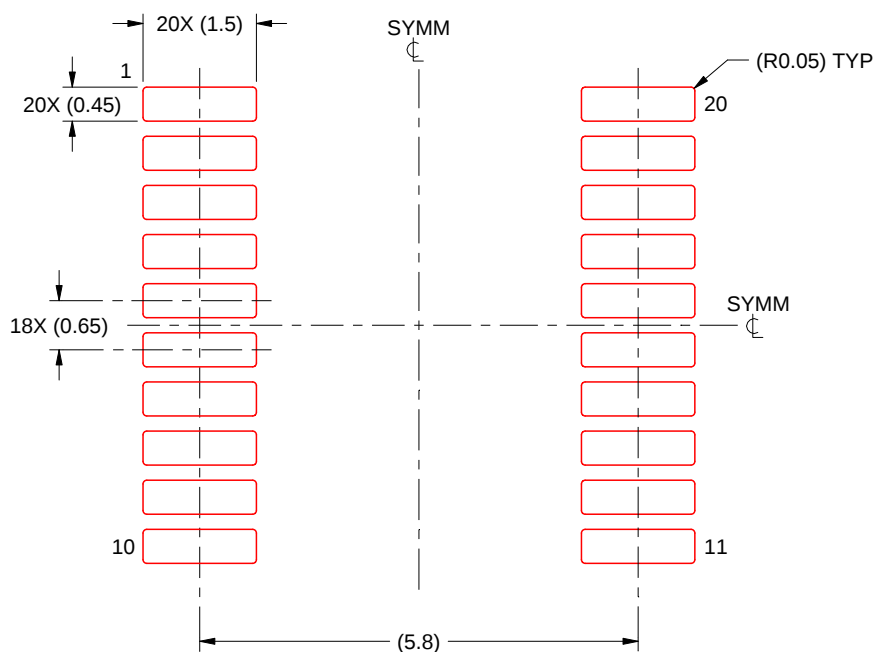
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

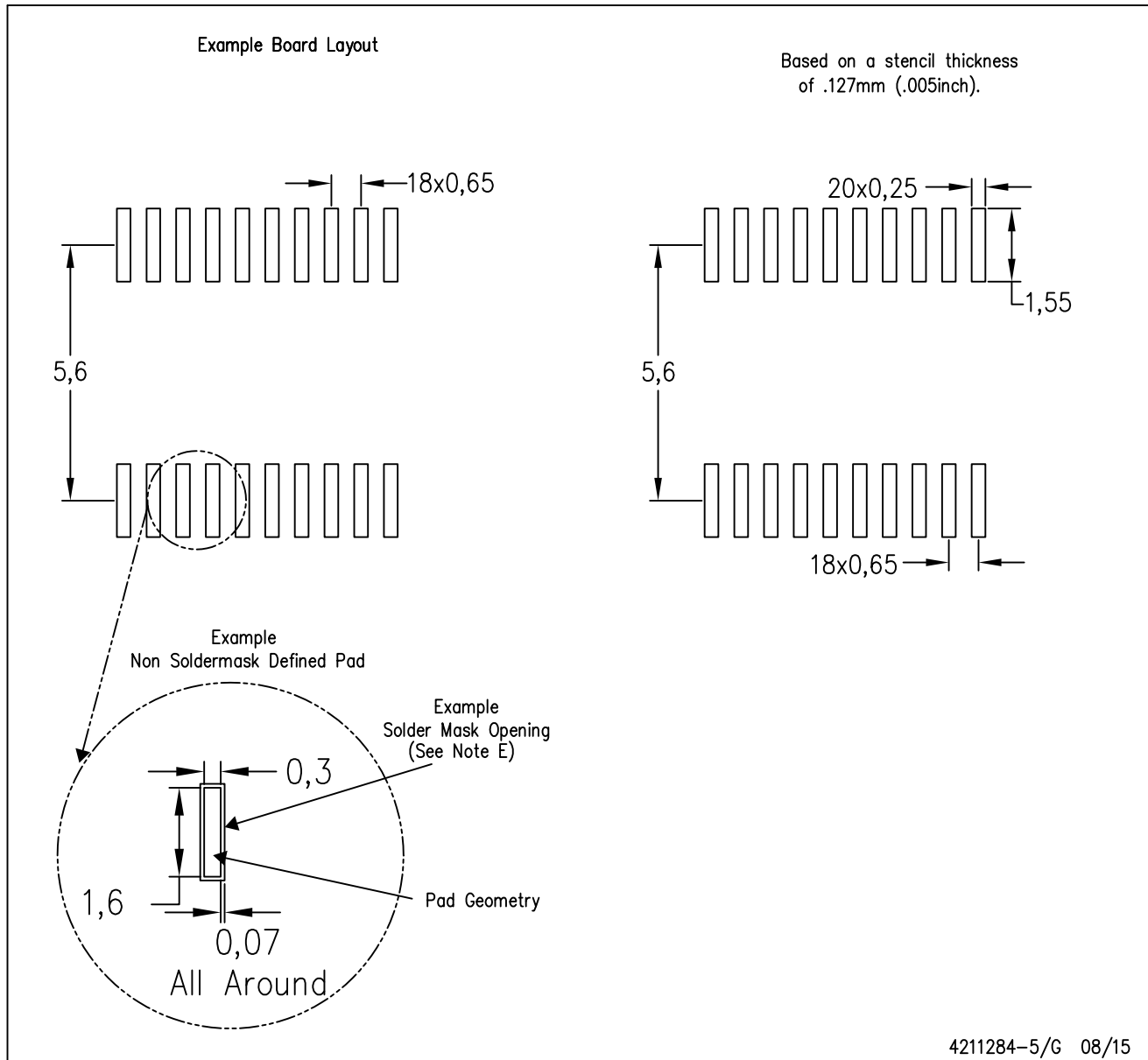
4220206/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate design.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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